General Purpose Transistor

PNP Silicon

PZT3906T1G

Features

• These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-40	Vdc
Collector – Base Voltage	V _{CBO}	-40	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Total Device Dissipation (Note 1) T _A = 25°C	P _D	1.5 12	W mW/°C	
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	83.3	°C/W	
Thermal Resistance Junction-to-Lead #4	$R_{\theta JA}$	35	°C/W	
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 with 1 oz and 713 mm² of copper area.



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ORDERING INFORMATION

Device	Package	Shipping [†]
PZT3906T1G	SOT–223 (Pb–Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Charac	teristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (Note 2)					
Collector – Emitter Breakdown Voltage (Note $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	2)	V _{(BR)CEO}	-40	-	Vdc
Collector – Base Breakdown Voltage $(I_C = -10 \ \mu Adc, I_E = 0)$		V _{(BR)CBO}	-40	_	
Emitter – Base Breakdown Voltage $(I_E = -10 \ \mu Adc, I_C = 0)$		V _{(BR)EBO}	-5.0	_	
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0 Vdc)		I _{BL}	_	-50	nAdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0 Vdc)		ICEX	_	-50	
ON CHARACTERISTICS (Note 2)					
$\label{eq:linear_state} \begin{array}{ c c c c } DC \ Current \ Gain \\ (I_C = -0.1 \ mAdc, \ V_{CE} = -1.0 \ Vdc) \\ (I_C = -1.0 \ mAdc, \ V_{CE} = -1.0 \ Vdc) \\ (I_C = -10 \ mAdc, \ V_{CE} = -1.0 \ Vdc) \\ (I_C = -50 \ mAdc, \ V_{CE} = -1.0 \ Vdc) \\ (I_C = -100 \ mAdc, \ V_{CE} = -1.0 \ Vdc) \end{array}$		H _{FE}	60 80 100 60 30	- - 300 - -	_
Collector – Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -1.0$ mAdc) ($I_C = -50$ mAdc, $I_B = -5.0$ mAdc)		V _{CE(sat)}		-0.25 -0.4	Vdc
Base – Emitter Saturation Voltage (I _C = -10 mAdc, I _B = -1.0 mAdc) (I _C = -50 mAdc, I _B = -5.0 mAdc)		V _{BE(sat)}	-0.65 -	-0.85 -0.95	
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = –10 mAdc, V _{CE} = –20 Vdc, f = 100 M	1Hz)	f _T	250	-	MHz
Output Capacitance (V _{CB} = -5.0 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	_	4.5	pF
Input Capacitance (V _{EB} = -0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	-	10	
Input Impedance (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f = 1.0 k	Hz)	h _{ie}	2.0	12	kΩ
Voltage Feedback Ratio (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f = 1.0 k	Hz)	h _{re}	0.1	10	X 10 ⁻⁴
Small – Signal Current Gain (I _C = –1.0 mAdc, V _{CE} = –10 Vdc, f = 1.0 k	Hz)	h _{fe}	100	400	-
Output Admittance ($I_C = -1.0$ mAdc, $V_{CE} = -10$ Vdc, f = 1.0 k	Hz)	h _{oe}	3.0	60	μmhos
Noise Figure (I _C = -100 μ Adc, V _{CE} = -5.0 Vdc, R _S = 1.0 kΩ, f = 1.0 kHz)		NF	_	4.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	(V _{CC} = -3.0 Vdc, V _{BE} = 0.5 Vdc,	t _d	-	35	
Rise Time	$I_{\rm C} = -10$ mAdc, $I_{\rm B1} = -1.0$ mAdc)	t _r	-	35	
Storage Time	(V _{CC} = -3.0 Vdc, I _C = -10 mAdc,	t _s	_	225	115
Fall Time	I _{B1} = I _{B2} = −1.0 mAdc)	t _f	_	75	

2. Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit Figure 2. Storage and Fall Time Equivalent Test Circuit



100

4

2

0

0.1 0.2 0.4

2.0

1.0

4.0

R_a, SOURCE RESISTANCE (k OHMS)

Figure 8.

I_C = 50 μA

I_C = 100 μA

40

100

20

10

10

20 40

SOURCE RESISTANCE = 2.0 k

2.0

1.0

4.0

f, FREQUENCY (kHz)

Figure 7.

1.0

0

0.1

I_C = 100 μA

0.2

0.4

h PARAMETERS

(V_CE = -10 Vdc, f = 1.0 kHz, T_A = 25 $^\circ C$)



Figure 11. Input Impedance

Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS









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